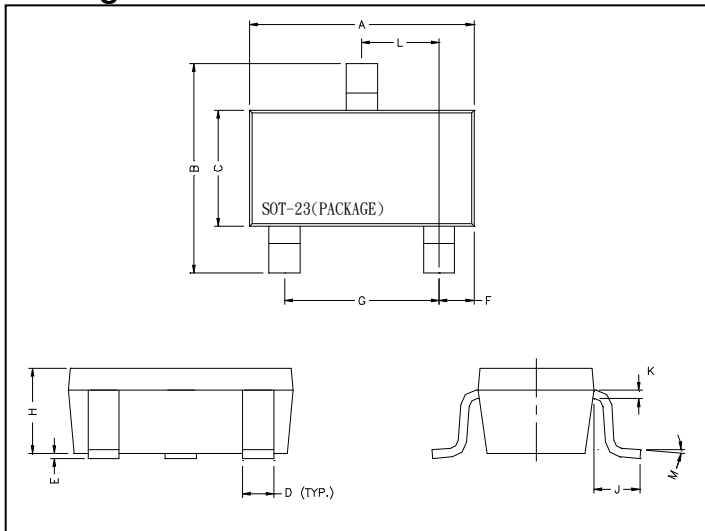


**GBAW56****SURFACE MOUNT, SWITCHING DIODE****Description**

The GBAW56 consists of two high-speed switching diodes with common anodes, fabricated in planar technology, and encapsulated in a small SOT-23 plastic SMD package.

**Package Dimensions**

Marking:

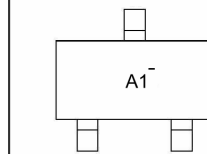
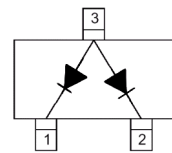


Diagram :

**Style: Pin 1.Cathode 2.Cathode 3. Common Anode**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

**Absolute Maximum Ratings at TA = 25°C**

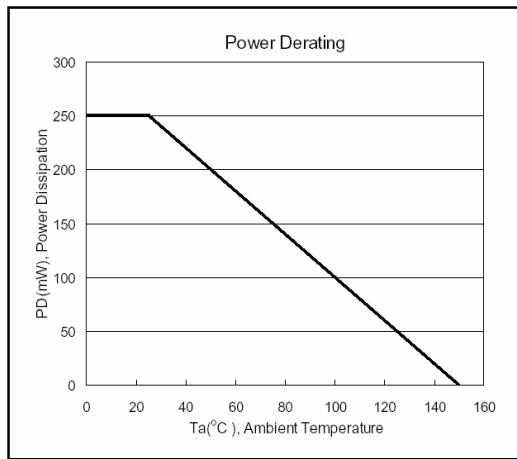
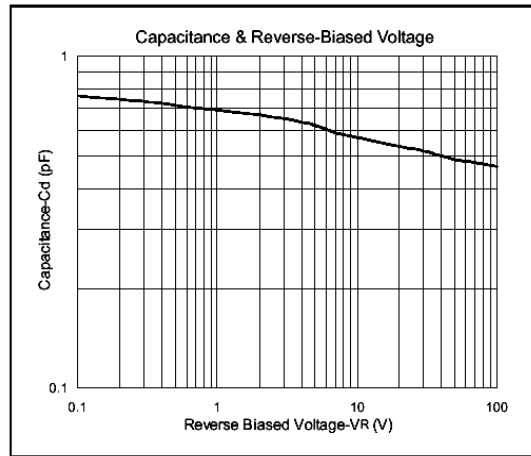
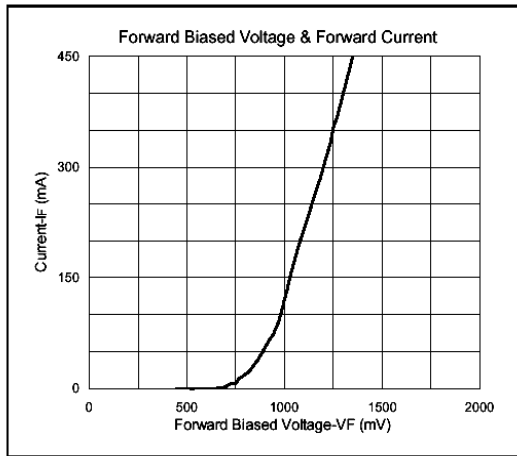
Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>j</sub>	+125	°C
Storage Temperature	T <sub>stg</sub>	-65 ~ +150	°C
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	85	V
Continuous Reverse Voltage	V <sub>R</sub>	75	V
Continuous Forward Current	single diode loaded (note1)	150	mA
	double diode loaded (note1)	130	
Repetitive Peak Forward Current	I <sub>FRM</sub>	500	mA
Non-Repetitive Peak Forward Current (1ms)	I <sub>FSM</sub>	1	A
Total Power Dissipation	P <sub>D</sub>	250	mW

Notes: 1. Device mounted on an FR4 printed-circuit board.

**Electrical Characteristics (at TA = 25°C unless otherwise noted)**

Parameter	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Voltage	V <sub>R</sub>	85	-	V	I <sub>R</sub> =100μA
Forward Voltage	V <sub>F</sub> (1)	-	715	mV	I <sub>F</sub> =1mA
	V <sub>F</sub> (2)	-	855	mV	I <sub>F</sub> =10mA
	V <sub>F</sub> (3)	-	1000	mV	I <sub>F</sub> =50mA
	V <sub>F</sub> (4)	-	1250	mV	I <sub>F</sub> =150mA
Reverse Current	I <sub>R</sub>	-	1	μA	V <sub>R</sub> =80V
Diode Capacitance	C <sub>D</sub>	-	2	pF	V <sub>R</sub> =0, f=1MHz
Reverse Recovery Time	T <sub>rr</sub>	-	4	nS	I <sub>F</sub> =I <sub>R</sub> =10mA, R <sub>L</sub> =100Ω measured at I <sub>R</sub> =1mA

## Characteristics Curve



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